Characterization and improved endurance for HfO\textsubscript{2} resistive memory with CMP treated TiN bottom electrode

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1. Introduction
Recently, binary oxide resistive memories (RM) with simple device structure, excellent scalability, and low power consumption, are considered as one of attractive candidates for next generation nonvolatile memory [1]. The authors proposed a reactive Ti overlay to modify the dielectric strength of HfO\textsubscript{2} film [2]. The Ti/HfO\textsubscript{2} RMs exhibit excellent bipolar resistive switching (BRS) with good retention and high speed as fast as 0.3 ns. Meanwhile, the surface roughness and stoichiometries of electrode were reported to influence the electrical properties of metal-insulator-metal capacitor [3,4]. We also adopted chemical mechanical polish (CMP) to flatten the bottom electrode (BE) [5], the endurance of the Ti/HfO\textsubscript{2} RM devices with a series resistor (1T1R) was greatly improved. However, the effects of CMP treated TiN BE on the structure of HfO\textsubscript{x} overlayer and the electrical properties one RM or 1T1R are still unclear. In this work, we comprehensively studied the impacts of CMP treated BE (CBE) on the microstructure and memory performance of HfO\textsubscript{x} based RM. A series resistor or a transistor was used to the endurance reliability of Ti/HfO\textsubscript{2} based RM with CBE by suppressing the current overshoot during forming/set step.

2. Device Fabrication and measurement
The bipolar RM devices were prepared through the stacked layers, which consisted of Ti/HfO\textsubscript{2}. TiN layer by sputtering were served as top electrode (TE) and BE, the detail process can be checked elsewhere [2], atomic layer deposition were adopted to deposit HfO\textsubscript{x} films of 5 nm-thick. The BE in some samples are treated with CMP process to smoothen the TiN layer, then regrow TiN to be the default thickness (50 nm). Some of the stacked films were annealed at post-metal annealing (PMA) of 450 °C for 5 min. The microstructure of the stacked structure was investigated by cross-sectional transmission electron microscopy (XTEM) operated at 200 keV. Grazing incident-angle X-ray diffraction (GIXRD) was adopted to characterize the crystal structure of HfO\textsubscript{x} films before/after PMA. X-ray photoelectron spectroscopy (XPS) was used to analyze the composition depth profile of the stacked layer. The memory devices with or without CBE with cell size ranging from 0.13 to 60 μm\textsuperscript{2} were fabricated, the devices are referred as 1R ones. A series resistor or transistor based on 0.18 μm technology was used to suppress the overshoot current in some devices (1T1R) during the forming process. The current-voltage (I-V) were characterized by using HP 4156A in sweep mode. 50 devices were measured to examine their electrical uniformity. The endurance of the 1R and 1T1R was studied by the stress mode of HP 4156A and pulse mode of 81110A.

3. Results and Discussion
The HRTEM micrograph of Ti/HfO\textsubscript{x} stacked layer upon BE and CBE under PMA are presented in Fig. 1. In the Fig. 1(b), there are some blurred regions at the interface of HfO\textsubscript{x} and CBE. The thickness of HfO\textsubscript{x} in both cases are the same, this results suggests that the growth rate of HfO\textsubscript{x} by ALD seems insensitive on the roughness of TiN BE. In Fig. 2, the crystallinity of HfO\textsubscript{x} films on different TiN BE before/after PMA were explored by GIXRD. For the as-prepared sample with CBE, the crystal structure of HfO\textsubscript{x} is amorphous. After PMA, the X-ray spectrum for the sample with CBE is partially crystalline, which is similar to that without CMP. But, the intensity of X-ray spectra originated from HfO\textsubscript{x} film upon CBE is lower than the latter. The surface roughness of the sample with TiN BE is ~ 1.1 nm, which is higher than that of CBE one (0.3 nm) as shown in Fig. 3. Oxygen (O) atoms distribution in as-grown and PMA for the sample of Ti/HfO\textsubscript{x} above CBE are depicted in Fig. 4. The Ti layer can effectively getter a lots of O atoms with the assistance of the successive PMA. In Fig. 5, the typical curves of leakage current and applied voltage for the 5-μm pristine RM with CBE from 27 to 180 °C are depicted. The inserted one shows the dependence of current density @ 1 V on the measurement figure of Fig. 6. At low bias (< 0.15 V), the carriers obey ohmic behavior and are dominated by space charge limited conduction (SCLC) under the bias between 0.15 and 0.35 V. At high E-field, the carriers follow the Fowler-Nordheim (F-N) tunneling. The devices show a better time dependent to breakdown property than that without CBE. The typical forming process and first reset I-V curves for the devices are shown (Fig. 7), the inserted one exhibits the typical BRS of the devices. The Weibull plots of the forming voltage (VF) distribution for the devices are presented in Fig. 8. In Fig. 9, the Weibull plot of the resistance of initial resistance state (IRS) and first RESET for the devices are presented. Owing to a high IRS magnitude of HfO\textsubscript{x} insulator with CBE, the RMs have a relative high VF (~ 2 V) and the lower resistance of first low resistance state (LRS) than that without CBE (Fig. 7). But the SET voltage and RESET voltage of the RM devices seem to be insensitive to the BE roughness (not shown here). The resistance of HRS and LRS for the device without CBE can be well resolved with a high resistance ratio (~ 100) after 3×10\textsuperscript{6} cycles as shown in Fig. 10. In contrast, the endurance of HfO\textsubscript{x} RM by using CBE is presented in Fig. 11. The HRS was degraded and both of the memory states for the device will merge after 10\textsuperscript{7} cycles. The excessive overshooting current in the RM during the forming or set step is responsible for this result. The excessive overshooting current in the CMP device with a series resistor (~ 800 Ω) can be suppressed during the forming (not shown here), but the memory window of endurance for the devices are improved ( > 10\textsuperscript{4} cycles, not shown here). With a series transistor as a perfect current limiter, the overshooting current in the CMP device during the repetitive forming/SET step can be effectively eliminated. Endurance of HfO\textsubscript{x} RMs with 1T1R configuration by using CBE in Fig. 12, the reversible on/off states with 40 ns switching speed can exceed up to 5×10\textsuperscript{7} cycles.

4. Conclusions
The microstructure of HfO\textsubscript{x} upon TiN with CMP and without CMP BE were investigated. Some nanocrystals embedded in amorphous matrix were observed in the HfO\textsubscript{x} films on CBE under PMA. CMP treated BE leads to the RM devices with high VF, low IRS current and low first LRS magnitude. High VF and the current overshoot may damage the HfO\textsubscript{x} RMs to suffer unstable switching during cycling test. The RM with an 800 Ω series resistor can enhance their endurance by alleviate the excessive overshooting current during forming. A series transistor as the selection device can suppress the current during the successive forming/SET step, the RMs with CBE show robust programming/erasing during the endurance test (> 5×10\textsuperscript{7} cycles).

5. References
Typical BRS characteristics of the devices.

When compared to devices with or without CBE, the inserted one is the TiN/Ti/HfOx above CMP treated TiN BE.

Oxygen atoms distribution in as-grown and PMA for the sample of HfOx/TiN above TiN BE.

The typical forming process and first reset I-V curves for the devices with or without CBE, the inserted one is the typical BRS characteristics of the devices.

The typical leakage current and applied voltage curves for the device with CBE from 27 to 180 °C. The inserted one shows the dependence of current density @ 1 V on the measurement temperature.

Endurance characteristics of HfOx resistive memory with 1T1R configuration by using CMP treated TiN BE.

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